

Product Overview

BD135: 1.5 A, 45V NPN Power Bipolar Junction Transistor

For complete documentation, see the data sheet.

This series of plastic, NPN Power Bipolar Junction Transistor transistors are designed for use as audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

Features

- Minimum Gain - $h_{FE} = 40$ @ $I_C = 150$ mA
- BD135, BD137, BD139 are complementary with BD136, BD138, BD140
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Benefits

- Low base drive

Applications

- Power supplies

End Products

- Power supplies

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Polarity	Type	$V_{CE(sat)}$ Max (V)	I_C Cont. (A)	V_{CEO} Min (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(on)}$ (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
BD135G	0.1735	Pb-free Halide free	Active	NPN	General Purpose	0.5	1.5	45					40	250	-	12.5	TO-225-3
BD135TG	0.2027	Pb-free Halide free	Active	NPN	General Purpose	0.5	1.5	45					40	250	-	12.5	TO-225-3

For more information please contact your local sales support at www.onsemi.com.

Created on: 6/3/2020